



PTO/SB/08A (08-03)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 2

of 5

Complete if Known

Application Number	10/678,438
Filing Date	3 October 2003
First Named Inventor	Vladimir V. MAKAROV
Art Unit	
Examiner Name	
Attorney Docket Number	65.0395

FOREIGN PATENT DOCUMENTS

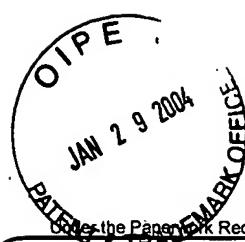
FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			

Examiner Signature		Date Considered	
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Complete if Known**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet 1 of 5

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Examiner Name	

Attorney Docket Number 65.0395

U. S. PATENT DOCUMENTS

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		US- 5,840,630	11-24-1998	Cecere et al.	
		US- 6,514,866 B2	02-04-2003	Russell et al.	
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		US- 5,959,358	09-28-1999	Lanford et al.	

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		JP2295117	12-06-1990	NTT	/	✓
		JP4173988	11-02-1990	Nissin Electric	✓	✓

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 3

of 5

Application Number	10/678,438
Filing Date	3 October 2003
First Named Inventor	Vladimir V. MAKAROV
Art Unit	
Examiner Name	
Attorney Docket Number	65.0395

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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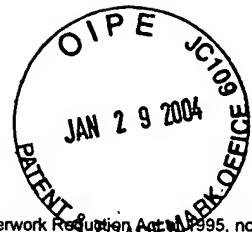
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(Use as many sheets as necessary)		Filing Date	3 October 2003
		First Named Inventor	Vladimir V. MAKAROV
		Art Unit	
		Examiner Name	
Sheet	4	of	5
		Attorney Docket Number	65.0395

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		J. Gonzalez et al, Improvements in Focused Ion Beam Micro-machining of Interconnect Materials, J. Vac. Sci. Technol. B20(6), Nov/Dec 2002, pp. 2700-2704	
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		S. Pauthner, Device modification and gass assisted etching on Cu-samples, 3rd European FIB Users Group Meeting (EFUG99) Abstracts 4 October 1999 (1 paragraph abstract of 8-page document)	
		2-Nitroethanol Material Safety Data Sheet, Aldrich Chemical Co., Inc., valid 02/2003-04/2003, (four pages)	

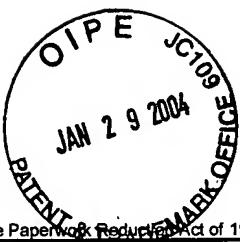
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		N. Goldblatt et al., Unique and Practical IC Timing Analysis Tool Utilizing Intrinsic Photon Emission, Microelectronics Reliability Conference, 2001, 41(9-10): 1507-1512	
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		C. Musil et al., Focused Ion Beam Microsurgery for Electronics, IEEE Electron Device Letters, 1986, EDL-7(5):285-287	

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